# National Semiconductor

The TP5089 is a low threshold voltage, field-implanted, metal gate CMOS integrated circuit. It interfaces directly to a

standard telephone keypad and generates all dual tone mul-

ti-frequency pairs required in tone-dialing systems. The tone

synthesizers are locked to an on-chip reference oscillator

using an inexpensive 3.579545 MHz crystal for high tone

accuracy. The crystal and an output load resistor are the

only external components required for tone generation. A

MUTE OUT logic signal, which changes state when any key

## **TP5089 DTMF (TOUCH-TONE) Generator**

#### **General Description**

is depressed, is also provided.

#### Features

- 3.5V-10V operation when generating tones
- 2V operation of keyscan and MUTE logic
- Static sensing of key closures or logic inputs
- On-chip 3.579545 MHz crystal-controlled oscillator
- Output amplitudes proportional to supply voltage
- High group pre-emphasis
- Low harmonic distortion
- Open emitter-follower low-impedance output
- SINGLE TONE INHIBIT pin



RRD-B30M115/Printed in U. S. A.

**TP5089 DTMF(TOUCH-TONE) Generator** 

December 1991

Absolute Maximum Ratings	i		
If Military/Aerospace specified devices a	are required,	Operating Temperature	-30°C to +60°C
please contact the National Semicond		Storage Temperature	$-55^{\circ}$ C to $+150^{\circ}$ C
Office/Distributors for availability and spe	cifications.	Maximum Power Dissipation	500 mW
Supply Voltage (V $_{ m DD}- m V_{SS}$ )	15V		
Maximum Voltage at Any Pin $V_{DD}$ + 0.3V t	to V <sub>SS</sub> $-$ 0.3V		

**Electrical Characteristics** Unless otherwise noted, limits printed in **BOLD** characters are guaranteed for  $V_{DD} = 3.5V$  to 10V,  $T_A = 0^{\circ}C$  to  $+60^{\circ}C$  by correlation with 100% electrical testing at  $T_A = 25^{\circ}C$ . All other limits are assured by correlation with other production tests and/or product design and characterization.

Parameter	Conditions	Min	Тур	Max	Units
Minimum Supply Voltage for Keysense and MUTE Logic Functions		2			v
Minimum Operating Voltage for generating tones		3.5			v
Operating Current Idle Generating Tones	Mute open $R_L = \infty$ $V_{DD} = 3.5V$		2 1.1	25 2.5	μA mA
Input Resistors COLUMN and ROW (Pull-Up) SINGLE TONE INHIBIT (Pull-Down) TONE DISABLE (Pull-Up)		25 120	50		kΩ kΩ
Input Low Level				0.2 V <sub>DD</sub>	V
Input High Level		0.8 V <sub>DD</sub>			V
MUTE OUT Sink Current (COLUMN and ROW Active)	$V_{DD} = 3.5V$ $V_0 = 0.5V$	0.4			mA
MUTE Out Leakage Current	$V_{o} = V_{DD}$		1		μΑ
Output Amplitude Low Group	$\begin{array}{c} R_{L} = 240 \; \Omega \\ V_{DD} = 3.5V \end{array}$	190	250	340	mVrms
	$R_{L} = 240\Omega$ $V_{DD} = 10V$	510	700	880	mVrms
Output Amplitude High Group	$\begin{array}{l} R_L = 240\Omega \\ V_DD = 3.5V \end{array}$	270	340	470	mVrms
	$\begin{array}{l} R_{L} = 240\Omega \\ V_{DD} = 10V \end{array}$	735	955	1265	mVrms
Mean Output DC Offset	$V_{DD} = 3.5V$ $V_{DD} = 10V$		1.3 4.6		V V
High Group Pre-Emphasis		2.2	2.7	3.2	dB
Dual Tone/Total Harmonic Distortion Ratio	$V_{DD} = 4V, R_L = 240\Omega$ 1 MHz Bandwidth		-23	-22	dB
Start-Up Time (to 90% Amplitude)			3	5	mS

Note 1:  $\mathsf{R}_\mathsf{L}$  is the external load resistor connected from TONE OUT to  $\mathsf{V}_{SS}.$ 

Note 2: Crystal specification: Parallel resonant 3.579545 MHz, R\_S  $\leq$  150  $\Omega,$  L = 100 mH, C\_O = 5 pF, C\_I = 0.02 pF.



### Functional Description (Continued)

TABLE I. Output Frequence	cy Accuracy
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Tone Valid Group Input			StandardTone OutputDTMF (Hz)Frequency		% Deviation from Standard	
	Low	R1	697	694.8	-0.32	
	Group	R2	770	770.1	+0.02	
	fL	R3	852	852.4	+0.03	
		R4	941	940.0	-0.11	
	High	C1	1209	1206.0	-0.24	
	Group	C2	1336	1331.7	-0.32	
	f <sub>H</sub>	C3	1477	1486.5	+0.64	
		C4	1633	1639.0	+0.37	

#### TABLE II. Functional Truth Table

SINGLE TONE	TONE	ROW	COLUMN	TONE OUT		MUTE
INHIBIT	DISABLE		COLONIN	Low	High	more
Х	0	O/C	O/C	0V	0V	O/C
Х	X	O/C	O/C	0V	0V	O/C
Х	0	One	One	Vos	Vos	0
Х	1	One	One	fL	f <sub>H</sub>	0
1	1	2 or More	One	-	f <sub>H</sub>	0
1	1	One	2 or More	fL	_	0
1	1	2 or More	2 or More	V <sub>OS</sub>	V <sub>OS</sub>	0
0	1	2 or More	One	V <sub>OS</sub>	V <sub>OS</sub>	0
0	1	One	2 or More	Vos	V <sub>OS</sub>	0
0	1	2 or More	2 or More	Vos	Vos	0

Note 1: X is don't care state.

Note 2:  $V_{OS}$  is the output offset voltage.





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